

# 60 V, 320 mA N-channel Trench MOSFET Rev. 1 — 12 August 2011

**Product data sheet** 

#### **Product profile** 1.

## 1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1.5 kV
- AEC-Q101 qualified

### 1.3 Applications

- Relay driver
- High-speed line driver

- Low-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C	-	-	60	V
$V_{GS}$	gate-source voltage		-20	-	20	V
$I_D$	drain current	$V_{GS} = 10 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	[1] -	-	320	mA
Static chara	cteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V; } I_D = 320 \text{ mA;}$ $T_j = 25 \text{ °C}$	-	1	1.6	Ω

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



# 2. Pinning information

Table 2. Pinning information

	_			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	3	D
3	D	drain	1	S 017aaa255

# 3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BSS138BKW	SC-70	plastic surface-mounted package; 3 leads	SOT323	

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BSS138BKW	AD%

<sup>[1]</sup> % = placeholder for manufacturing site code.

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C	-	60	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u> -	320	mΑ
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	<u>[1]</u> -	210	mA
I <sub>DM</sub>	peak drain current	$T_{amb} = 25 \text{ °C}$ ; single pulse; $t_p \le 10 \text{ µs}$	-	1.2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2] -	260	mW
			[1] -	310	mW
		T <sub>sp</sub> = 25 °C	-	830	mW
Tj	junction temperature		-55	150	°C
T <sub>amb</sub>	ambient temperature		-55	150	°C
T <sub>stg</sub>	storage temperature		-65	150	°C
Source-drai	in diode				
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u> _	320	mA
ESD maxim	um rating				
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	<u>[3]</u> _	1500	V

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

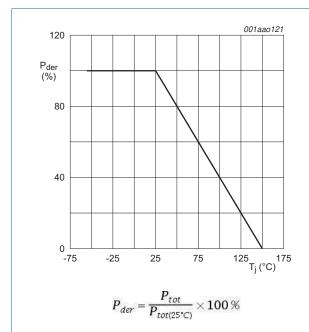


Fig 1. Normalized total power dissipation as a function of junction temperature

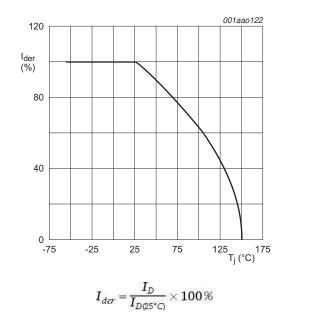
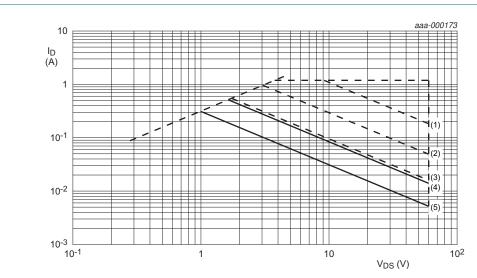


Fig 2. Normalized continuous drain current as a function of junction temperature



 $I_{\text{DM}}$  is a single pulse

- (1)  $t_p = 1 \text{ ms}$
- (2)  $t_p = 10 \text{ ms}$
- (3)  $t_p = 100 \text{ ms}$
- (4) DC;  $T_{sp} = 25 \, ^{\circ}\text{C}$
- (5) DC; T<sub>amb</sub> = 25 °C; 1 cm<sup>2</sup> drain mounting pad

Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source Fig 3. voltage

#### Thermal characteristics

**Thermal characteristics** Table 6.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to amb	ient in free air	<u>[1]</u> _	415	480	K/W
			[2] _	350	400	K/W
$R_{th(j-sp)}$	thermal resistance from junction to sold point	er	-	-	150	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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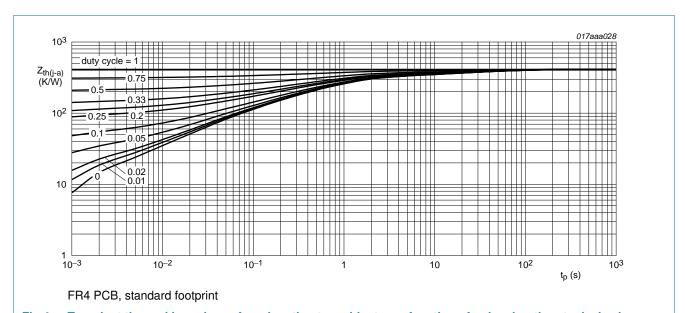


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

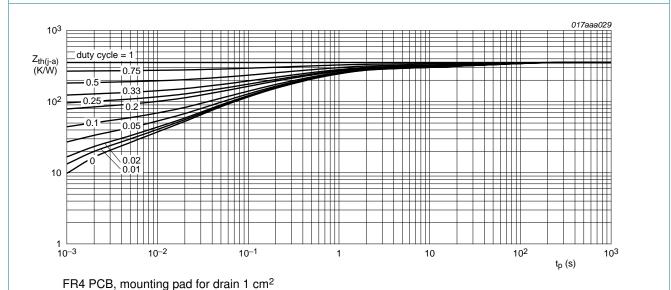


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.48	1.1	1.6	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	10	μΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	10	μΑ
		$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
$R_{DSon}$	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 320 \text{ mA}; T_j = 25 \text{ °C}$	-	1	1.6	Ω
	resistance	$V_{GS} = 10 \text{ V}; I_D = 320 \text{ mA}; T_j = 150 \text{ °C}$	-	2	3.2	Ω
		$V_{GS}$ = 4.5 V; $I_D$ = 200 mA; $T_j$ = 25 °C	-	1.1	2.2	Ω
		$V_{GS} = 2.5 \text{ V}; I_D = 10 \text{ mA}; T_j = 25 \text{ °C}$	-	1.4	6.5	Ω
g <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	700	-	mS
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 300 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	0.6	0.7	nC
$Q_{GS}$	gate-source charge	$T_j = 25  ^{\circ}C$	-	0.1	-	nC
$Q_{GD}$	gate-drain charge		-	0.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	42	56	рF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	7	-	рF
$C_{rss}$	reverse transfer capacitance		-	4	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 40 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = 10 V;	-	5	10	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	38	76	ns
t <sub>f</sub>	fall time		-	20	-	ns
Source-di	rain diode					
$V_{SD}$	source-drain voltage	$I_S = 300 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	0.47	0.8	1.2	V

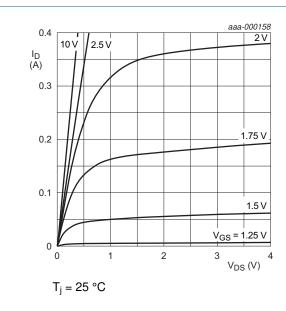
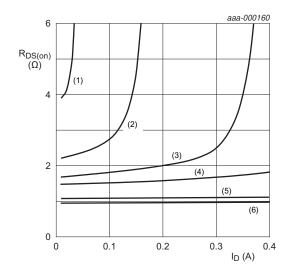


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$ 

(1)  $V_{GS} = 1.5 \text{ V}$ 

(2)  $V_{GS} = 1.75 \text{ V}$ 

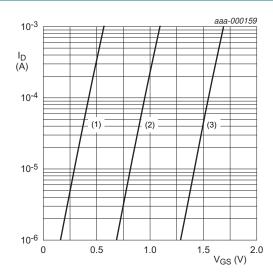
(3)  $V_{GS} = 2.0 \text{ V}$ 

(4)  $V_{GS} = 2.25 \text{ V}$ 

(5)  $V_{GS} = 4.5 \text{ V}$ 

(6)  $V_{GS} = 10 \text{ V}$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



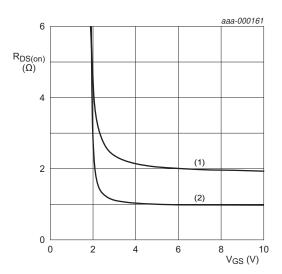
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage

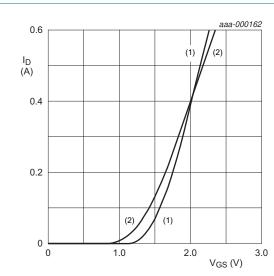


 $I_D = 300 \text{ mA}$ 

(1)  $T_j = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

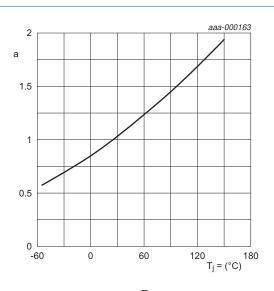


 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_i = 25 \, ^{\circ}C$$

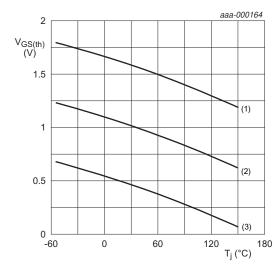
(2) 
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

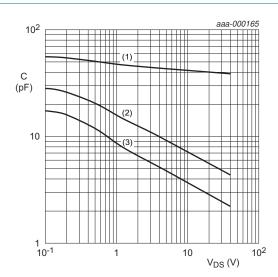
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



f = 1 MHz; V<sub>GS</sub> = 0 V

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

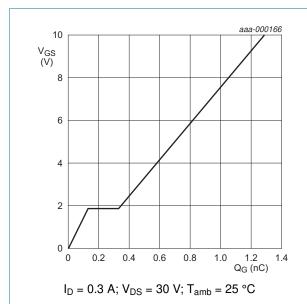


Fig 14. Gate-source voltage as a function of gate charge; typical values

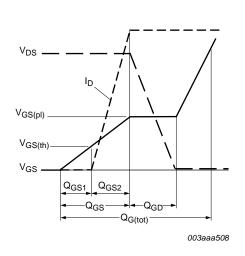
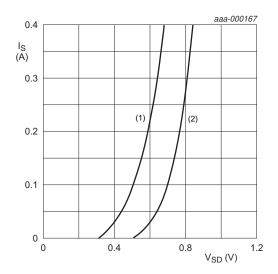


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ 

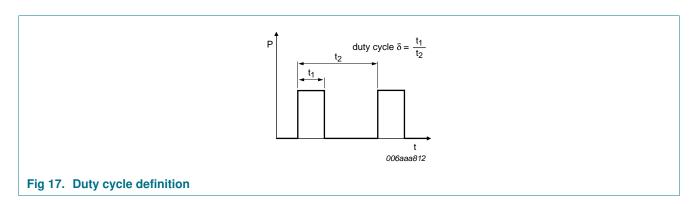
(1)  $T_j = 150 \, ^{\circ}C$ 

(2)  $T_j = 25 \, {}^{\circ}\text{C}$ 

Fig 16. Source current as a function of source-drain voltage; typical values

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# 8. Test information



# 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 9. Package outline

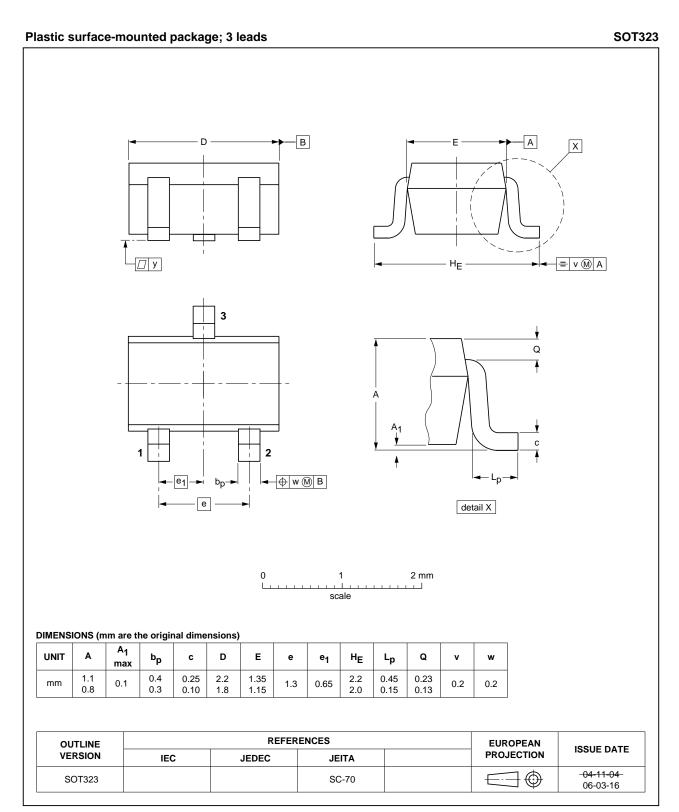
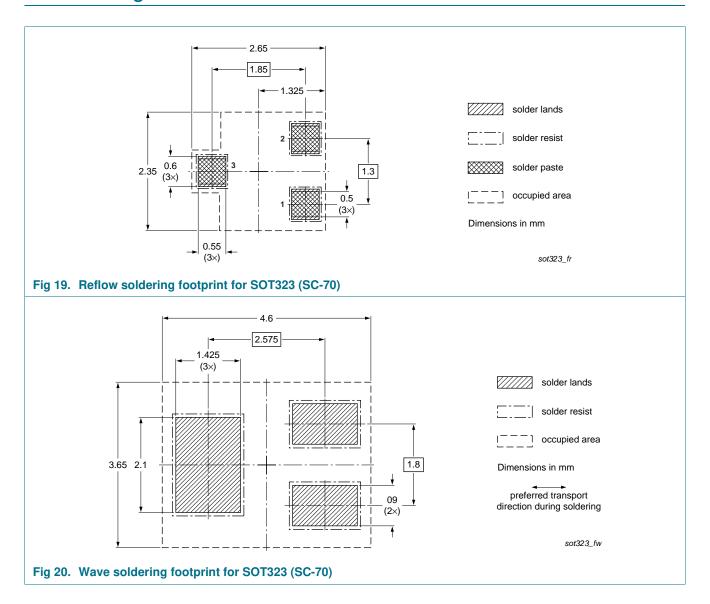


Fig 18. Package outline SOT323 (SC-70)

# 10. Soldering



Nexperia BSS138BKW

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# 11. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS138BKW v.1	20110812	Product data sheet	-	-

# 12. Legal information

#### 12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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